INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known	
Application Number	10/670,928
Filing Date	September 25, 2003
First Named Inventor	Chun-Li Liu et al.
Group Art Unit	2812
Examiner Name	Unassigned
Attorney Docket Number	SC12851ZP

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. [1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
DL	B1	5,534,713	07/09/1996	Ismail *et al.*	
	B2	5,846,857	12/08/1998	Ju	
	B3	5,943,565	08/24/1999	Ju	
	B4	5,998,807	12/07/1999	Lustig *et al.*	
	B5	6,059,895	05/09/2000	Chu *et al.*	
	B6	6,124,627	09/26/2000	Rodder *et al.*	
	B7	2001/0048119 A1	12/06/2001	Mizuno *et al.*	
	B8	6,339,232 B1	01/15/2002	Takagi	
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Examiner Initials*	Cite No. [1]	Foreign Patent Document Country Code[3] Number [4] Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[5]
DL	B11	PCT – WO 02/45156 A2	06/06/2002	Armstrong *et al.*		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[5]
DL	B12	Jung *et al.*, "Implementation of Both High-Hole and Electron Mobility in Strained Si/Strained $Si_{1-y}Ge_y$ on Relaxed $Si_{1-x}Ge_x$(x<y) Virtual Substrate," *IEEE Electron Device Letters*, Vol. 24, No. 7, July 2003, pp. 460-462.	
	B13	Tezuka *et al.*, "Ultrathin Body SiGe-on-Insulator pMOSFETs with High-Mobility SiGe Surface Channels," *IEEE Transactions on Electron Devices*, Vol. 50, No. 5, May 2003, pp. 1328-1333.	

Examiner Signature	DL	Date Considered	4/2005

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SC12851ZP

PTO/SB/08A (04-03)

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known	
Application Number	10/670928
Filing Date	
First Named Inventor	Chun-Li Liu
Group Art Unit	2818
Examiner Name	D. LE
Attorney Docket Number	SC12851ZP

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Examiner Initials*	Cite No. [1]	Document Number Number -Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
DL	AA	5,461,243	10/24/1995	Ek *et al.*	
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	AE	2003/0013305 A1	01/16/2003	Sugii *et al.*	
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Examiner Initials*	Cite No. [1]	Foreign Patent Document Country Code[3] Number [4] Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T [5]
DL	AH	JP 2000243946	12/06/1999	Naoharu *et al.*		Yes/Abstract
	AI	WO 02/33746 A1	04/22/2002	Chu *et al.*		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
DL	AJ	Chi *et al.*, "Electrically active defects in surface preamorphized and subsequently RTP-annealed Si and the effect of titanium silicidation," *Proc. 1998 5th International Conference on Solid-State and Integrated Circuit Technology*,", October 21, 1998, Beijing, China, p. 324-327.	✓
	AK	Fahey *et al.*, "Point defects and dopant diffusion in silicon," *Reviews of Modern Physics*, April 1989, Vol. 61, No. 2, pp. 289-384.	
	AL	Lee *et al.*, "Sub-30 nm P+ abrupt junction formation in Strained Si/Si$_{1-x}$Ge$_x$ MOS device," *Technical Digest of the International Electron Devices Meeting*, December 8, 2002, pp. 379-81.	
	AM	LeGoues *et al.*, "Kinetics and Mechanism of Oxidation of SiGe: Dry Versus Wet Oxidation," *Applied Physics Letters*, February 13, 1989, Vol. 54, No. 7, pp. 644-646.	
	AN	LeGoues *et al.*, "Oxidation Studies of SiGe," *Journal of Applied Physics*, February 15, 1989, Vol. 65, No. 4, pp. 1724-1728.	
	AO	Lim *et al.*, "Dry Thermal Oxidation of a Graded SiGe Layer," *Applied Physics Letters*, November 26, 2001, Vol. 79, No. 22, pp. 3606-3608.	
	AP	Sawano *et al.*, "Relaxation Enhancement of SiGe Thin Layers by Ion Implantation into Si Substrates," *IEEE*, 2002, pp. 403-404.	
	AQ	Tezuka *et al.*, "Dislocation-free Formation of Relaxed SiGe-on-insulator Layers," *Applied Physics Letters*, May 13, 2002, Vol. 80, No. 19, pp. 3560-3562.	
	AR	Tezuka *et al.*, "Fabrication of Strained Si on an Ultrathin SiGe-on-Insulator Virtual Substrate with a High-Ge Fraction," *Applied Physics Letters*, September 17, 2001, Vol. 79, No. 12, pp. 1798-1800.	
DL	AS	Vyatkin *et al.*, "Ion Beam Induced Strain Relaxation in Pseudomorphous Epitaxial SiGe Layers," *IEEE*, 2000, pp. 70-72.	

Examiner Signature	DL	Date Considered	Feb-2005

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